

# Huadong Gan

## List of Publications by Year in descending order

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20  
papers

3,508  
citations

932766

10  
h-index

752256

20  
g-index

20  
all docs

20  
docs citations

20  
times ranked

3270  
citing authors

#	ARTICLE	IF	CITATIONS
1	High performance perpendicular magnetic tunnel junction with Co/Ir interfacial anisotropy for embedded and standalone STT-MRAM applications. Applied Physics Letters, 2018, 112, .	1.5	34
2	Perpendicular magnetic tunneling junction switching dynamic modes, extreme events, and performance scaling. Applied Physics Letters, 2017, 110, .	1.5	2
3	Zero-field spin transfer oscillators based on magnetic tunnel junction having perpendicular polarizer and planar free layer. AIP Advances, 2016, 6, 125305.	0.6	8
4	Perpendicular magnetic tunnel junction with thin CoFeB/Ta/Co/Pd/Co reference layer. Applied Physics Letters, 2014, 105, 192403.	1.5	24
5	Different dielectric breakdown mechanisms for RF-MgO and naturally oxidized MgO. Applied Physics Express, 2014, 7, 083002.	1.1	9
6	Dramatic reduction of read disturb through pulse width control in spin torque random access memory. Applied Physics Letters, 2013, 103, 142419.	1.5	2
7	RECENT PROGRESS OF PERPENDICULAR ANISOTROPY MAGNETIC TUNNEL JUNCTIONS FOR NONVOLATILE VLSI. Spin, 2012, 02, 1240003.	0.6	63
8	Boron Composition Dependence of Magnetic Anisotropy and Tunnel Magnetoresistance in MgO/CoFe(B) Based Stack Structures. IEEE Transactions on Magnetics, 2012, 48, 3829-3832.	1.2	28
9	Tunnel Magnetoresistance Properties of Double MgO-Barrier Magnetic Tunnel Junctions With Different Free-Layer Alloy Compositions and Structures. IEEE Transactions on Magnetics, 2011, 47, 1567-1570.	1.2	10
10	Ferromagnetic nature of (Ga, Cr)As epilayers revealed by magnetic circular dichroism. Solid State Communications, 2011, 151, 456-459.	0.9	8
11	Origin of the collapse of tunnel magnetoresistance at high annealing temperature in CoFeB/MgO perpendicular magnetic tunnel junctions. Applied Physics Letters, 2011, 99, .	1.5	55
12	A perpendicular-anisotropy CoFeB/MgO magnetic tunnel junction. Nature Materials, 2010, 9, 721-724.	13.3	3,020
13	Tunnel magnetoresistance properties and film structures of double MgO barrier magnetic tunnel junctions. Applied Physics Letters, 2010, 96, .	1.5	49
14	MgO barrier-perpendicular magnetic tunnel junctions with CoFe/Pd multilayers and ferromagnetic insertion layers. Applied Physics Letters, 2009, 95, .	1.5	130
15	Perpendicular Magnetic Tunnel Junctions with CoFe/Pd Multilayer Electrodes and an MgO Barrier. IEEE Transactions on Magnetics, 2009, 45, 3476-3479.	1.2	19
16	Growth Parameter Dependence of Structural Characterizations of Diluted Magnetic Semiconductor (Ga, Cr)As. IEEE Transactions on Magnetics, 2008, 44, 2692-2695.	1.2	3
17	Influences of As flux on the lattice constants, magnetic and transport properties of (Ga, Mn)As epilayers. Solid State Communications, 2007, 141, 453-458.	0.9	2
18	Two opposite gradients of hole density in as-grown and annealed (Ga,Mn)As layers. Journal of Magnetism and Magnetic Materials, 2007, 308, 313-317.	1.0	4

#	ARTICLE	IF	CITATIONS
19	Photocurrent response in a double barrier structure with quantum dotsâ€“quantum well inserted in central well. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 33, 355-358.	1.3	34
20	Photoinduced voltage shift in a three-barrier, two-well resonant tunneling structure integrated with a 1.2- $\mu$ m-thick n-type GaAs layer. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 28, 242-246.	1.3	4